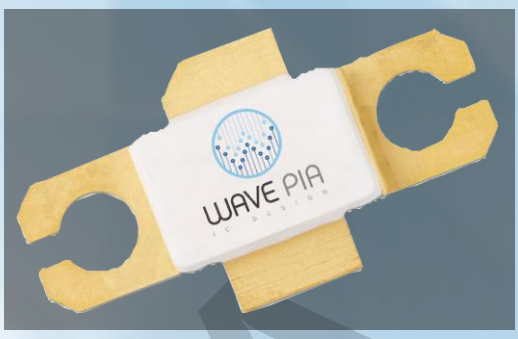
WP284P5015UH

15W RF GaN Power Transistor

Product Features

- Up to 6 GHz Operation
- 12.7 dB Small Signal Gain at 4.6 GHz
- 21.6W Typical P_{sat} at 4.6 GHz
- 60.7 % Efficiency at P_{sat} at 4.5 GHz
- 28 V Operation



Applications

- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- WiMAX, LTE, WCDMA, GSM
- Radar application

Absolute Maximum Ratings

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	160	Volts	25˚C
Gate-to-Source Voltage[3]	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature[3]	T_{STG}	-65, +150	˚C	
Operating Junction Temperature[1,3]	T_J	225	˚C	
Maximum Forward Gate Current[3]	I_{GMAX}	30	mA	25˚C
Maximum Drain Current[2]	I_{DMAX}	1	A	Id@ Vd =10V, Vg= 1V
Soldering Temperature[3]	T_S	245	˚C	
Storage Temperature[3]	T_{STG}	-65, +150	˚C	

Note:
1. Continuous use at maximum temperature will affect MTTF.
2. Current limit for long term, reliable operation
3. After additional updates

DC Characteristics[1] (TC = 25°C)

Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Gate Threshold Voltage	$V_{GS(th)}$		-3.1		V_{DC}	VDS = 10 V, ID = 1 mA
Gate Quiescent Voltage	$V_{GS(Q)}$		-2.26		V_{DC}	VDS = 28 V, ID = 150 mA
Saturated Drain Current[2]	I_{DS}		1000		mA/mm	VDS = 10 V, VGS = 1 V
Drain-Source Breakdown Voltage	V_{BR}	160			V_{DC}	ID = 1 mA/mm

Note:
1. Measured on wafer prior to packaging.
2. Scaled from PCM data.

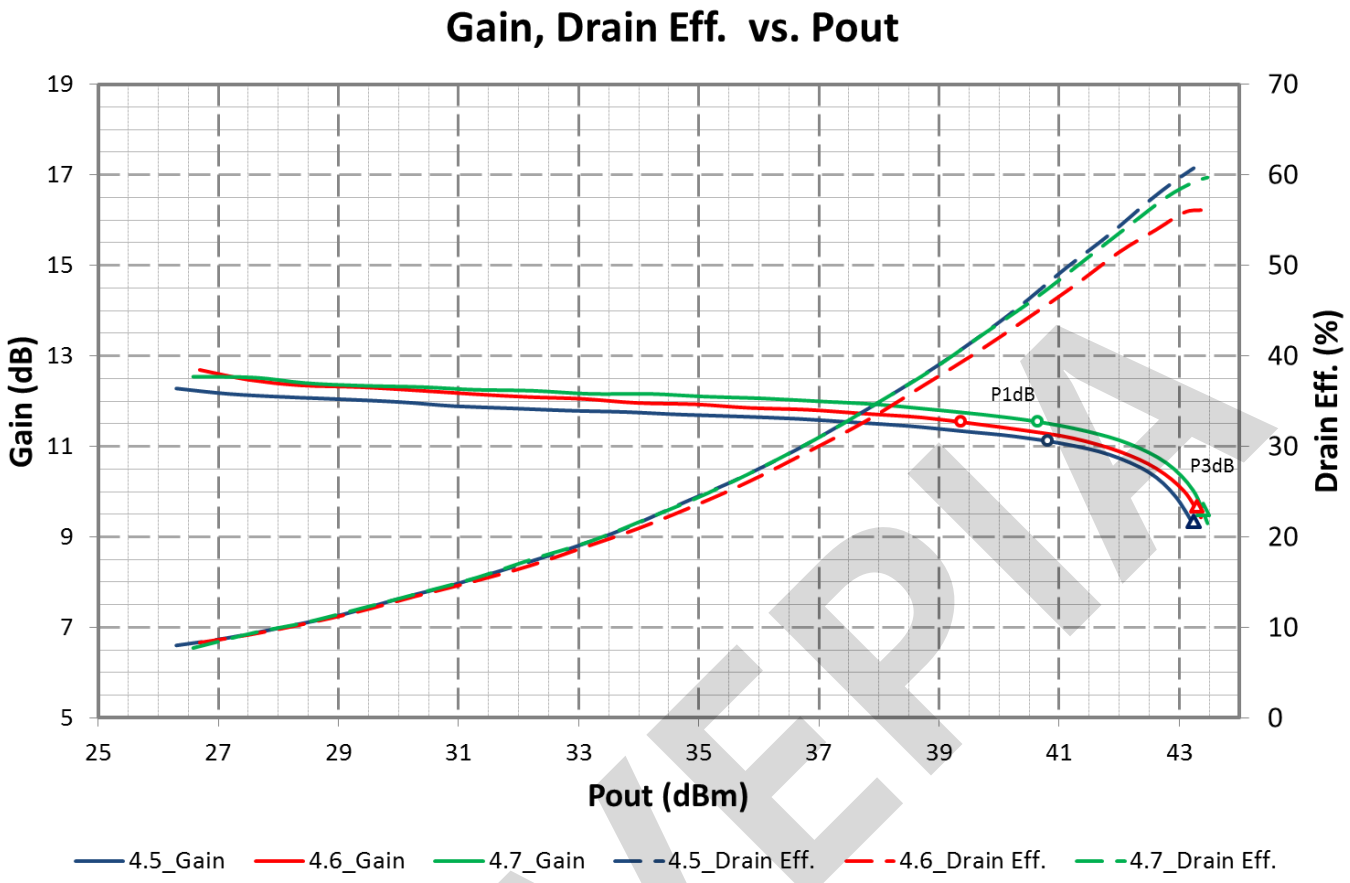
RF Characteristics (TC = 25°C, F0 = 4.6 GHz unless otherwise noted)

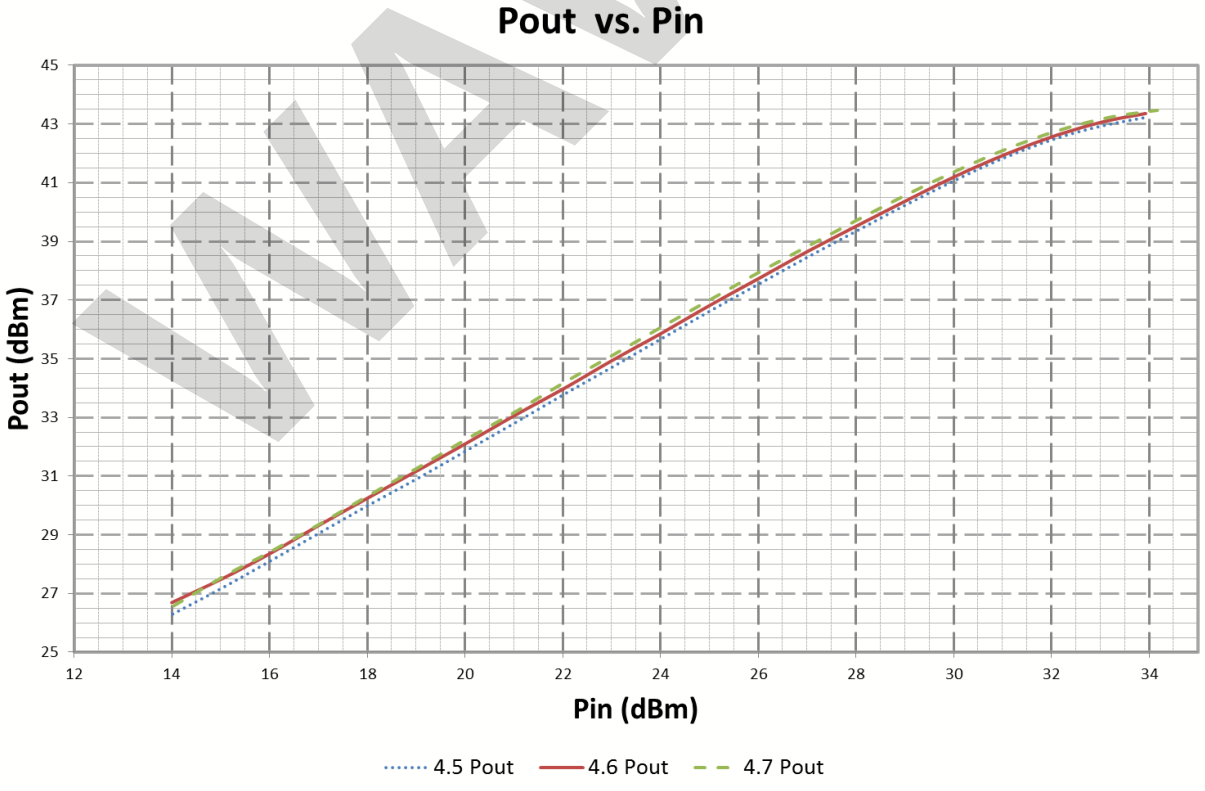
Parameter	Symbol	MIN	TYP	MAX	Units	Conditions
Power Gain	G_{SS}		11.6		dB	VDD = 28 V, IDQ = 150 mA, Pulse Width = 100 usec, Duty Cycle = 10%
Output Power	P_{OUT}		8		W	VDD = 28 V, IDQ = 150 mA, Pulse Width = 100 usec, Duty Cycle = 10%
Saturated Output Power	P_{SAT}		21.6		W	VDD = 28 V, IDQ = 150 mA, Pulse Width = 100 usec, Duty Cycle = 10%
Pulsed Drain Efficiency[1]	η		56.1		%	VDD = 28 V, IDQ = 150 mA, Pulse Width = 100 usec, Duty Cycle = 10% @ Psat
Output Mismatch Stress	VSWR	-	-	10:1		No damage at all phase angles, VDD = 28 V, IDQ = 150 mA, POUT = 2 WCW

Note:
1. Drain Efficiency = P_{OUT}/P_{DC}

Pulse Signal Performance (Tc=25℃, Measured in the test board amplifier circuit)

VDD = 28 V, IDQ = 150 mA, PulseWidth = 100µsec, Duty Cycle = 10%





Small Signal Performance (Tc=25℃, Measured in the test board amplifier circuit)

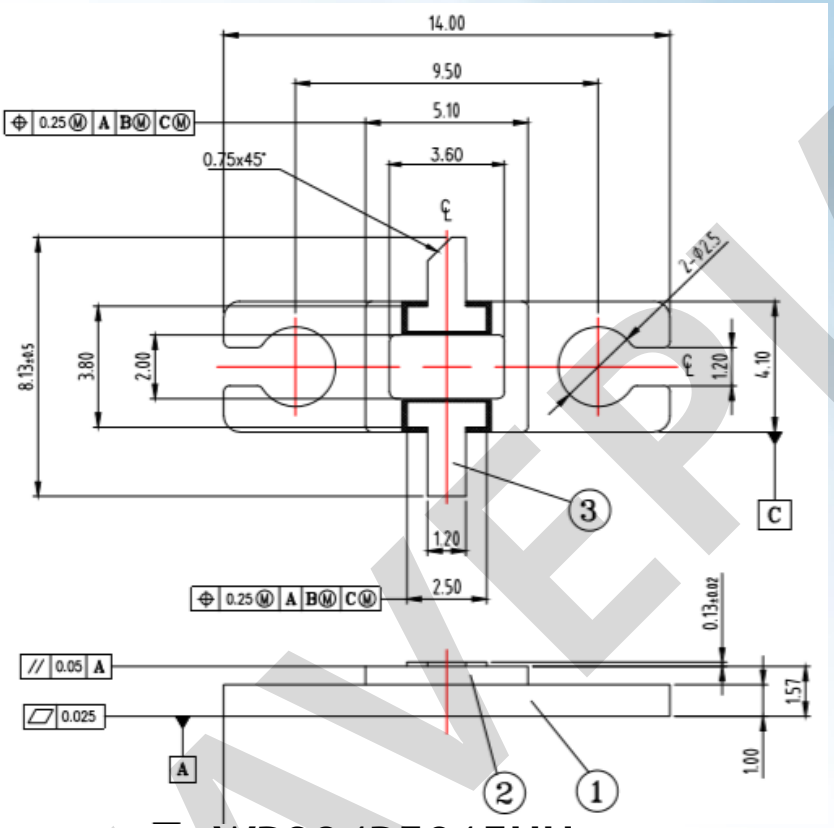
VDD = 28 V, IDQ = 150 mA,

Part number code

WP284P5015UH

- S (Surface), H (Screw Hole)
- M (Matched), U (Unmatched)
- Power (Watt)
- Frequency (GHz)
- Drain Voltage (DC)

Package Dimensions



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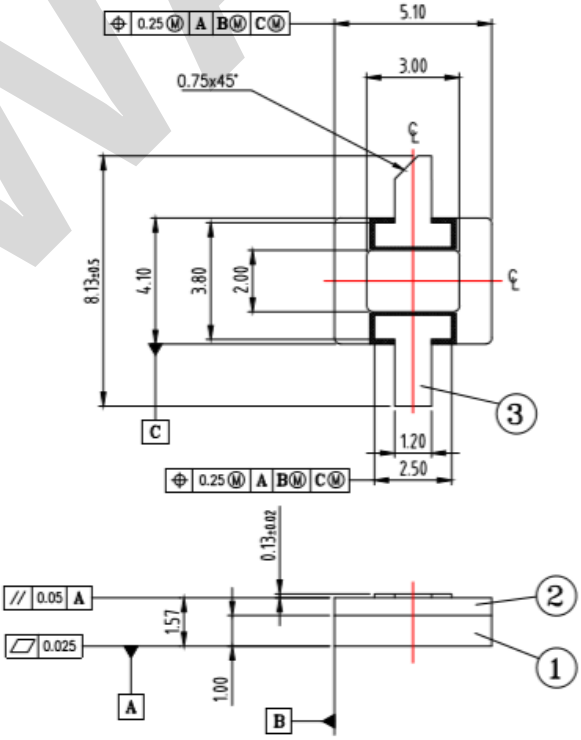

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WAVE PIA
IC DESIGN

#1301, 557, Dongtangiheung-ro,
Hwaseong-si, Gyeonggi-do,
South Korea
Tel : 82-31-8058-3374
82-31-8058-3384
Fax : 82-31-8058-3302
E-mail : platune@wavepia.com
yohwang@wavepia.com
Website: www.wavepia.com